

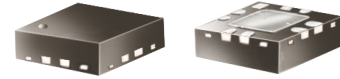
High Directivity

Monolithic Amplifier

0.5-2.5 GHz

Product Features

- 2.8V & 5V operation
- Micro-miniature size .120"X.120"
- Internal DC blocking at RF input and output
- High directivity, 17 dB typ.
- Low noise figure
- Output power, up to +12.2 dBm typ.
- Excellent repeatability
- Low cost
- Aqueous washable



MNA-5+

CASE STYLE: DQ849
PRICE: \$1.60 ea. QTY. (30)

+ RoHS compliant in accordance
with EU Directive (2002/95/EC)

The +Suffix has been added in order to identify RoHS Compliance. See our web site for RoHS Compliance methodologies and qualifications.

Typical Applications

- Buffer amplifier
- Cellular
- PCN
- Communications satellite
- Defense

General Description

MNA-5+ is a wideband amplifier offering high dynamic range. It has repeatable performance from lot to lot. It is enclosed in a 3x3 mm MCLP plastic package. MNA-5+ is fabricated using GaAs MESFET technology. Expected MTBF at 85°C case temperature is 120,000 years at 2.8V; 60,000 years at 5V.

Function	Pin Number	Description
RF IN	2	RF input pin
RF-OUT	5	RF output pin
DC	7, with 1000 pF bypass to ground; connect pin 8 via 33 ohms to pin 7 externally	Bias pins
GND	3,4 and paddle in center of bottom	Connections to ground
OPTIONAL	1,6	No internal connection; recommended use: per PCB Layout PL-078



P.O. Box 350166, Brooklyn, New York 11235-0003 (718) 934-4500 Fax (718) 332-4661 For detailed performance specs & shopping online see Mini-Circuits web site



The Design Engineers Search Engine Provides ACTUAL Data Instantly From MINI-CIRCUITS At: www.minicircuits.com

RF/IF MICROWAVE COMPONENTS

REV. L
M108520
MNA-5+
080305
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Electrical Specifications at 25°C

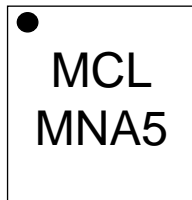
Parameter	Min.	Typ.		Max.	Units	
Frequency Range	0.5			2.5	GHz	
at DC Volts	2.8	5.0	2.8	5.0	V	
Gain	17.0	f=0.5 GHz	18.5	18.0	dB	
		f=1.0 GHz	22.8	21.4		
		f=1.5 GHz	21.9	20.5		
		f=2.0 GHz	20.6	19.4		
		f=2.5 GHz	18.0	17.4		
Input Return Loss	f=0.75-2.5 GHz	12.5	12.5		dB	
Output Return Loss	f=0.75-2.5 GHz	10	10		dB	
Output Power @ 1 dB compression	f=0.5 GHz f=2.5GHz	12.2 8.0	10.1 6.5		dBm	
Output IP3	f=1 GHz f=2 GHz	19.4 21.0	18.0 20.0		dBm	
Noise Figure	f=1 GHz	3.5			dB	
Directivity (Isolation - Gain)			17			
DC Current			28	26	40	mA
Thermal Resistance, junction-to-case			78		°C/W	

Absolute Maximum Ratings

Parameter	Ratings
Operating Temperature	-40°C to 85°C
Storage Temperature	-55°C to 100°C
DC Voltage	7V at pin 7 10V at pins 2 & 5
Power Dissipation	500mW
Input Power	10dBm

Note: Permanent damage may occur if any of these limits are exceeded. These ratings are not intended for continuous normal operation.

Product Marking



Additional Detailed Technical Information

Additional information is available on our web site. To access this information enter the model number on our web site home page.

Performance data, graphs, s-parameter data set (.zip file)

Case Style: DQ849

MNA-5+: Plastic package, exposed paddle, lead finish: tin/silver/nickel

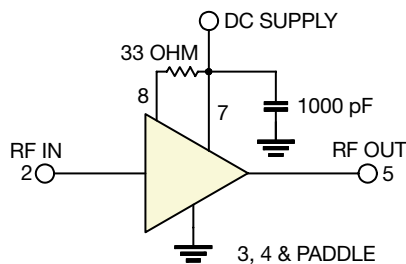
Tape & Reel: F66

Suggested Layout for PCB Design: PL-078

Evaluation Board: TB-186+

Environmental Ratings: ENV08T1

Recommended Application Circuit



ESD Rating

Human Body Model (HBM): Class 1A (250v to < 500v) in accordance with ANSI/ESD STM 5.1 - 2001

Charged Device Model (CDM): Class III (500 to 1000v) in accordance with JESD22-C101A

MSL Rating

Moisture Sensitivity: MSL1 in accordance with IPC/JEDEC J-STD-020C

No.	Test Required	Condition	Standard	Quantity
1	Visual Inspection	Low Power Microscope Magnification 40x	MIP-IN-0003 (MCT spec)	45 units
2	Electrical Test	Room Temperature	SCD (MCL spec)	45 units
3	SAM Analysis	Less than 10% growth in term of delamination	J-Std-020C (Jedec Standard)	45 units
4	Moisture Sensitivity Level 1	Bake at 125°C for 24 hours Soak at 85°C/85%RH for 168 hours Reflow 3 cycles at 260°C peak	J-Std-020C (Jedec Standard)	45 units

MSL Test Flow Chart

